# AC6329E Datasheet

# Zhuhai Jieli Technology Co.,LTD

Version: V1.3

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### **AC6329E** Features

#### **High performance 32-bit RISC CPU**

- RISC 32-bit CPU
- DC-96MHz operation
- 73KB data RAM
- 8KB I-cache 2way
- 1KB Rocache 1way
- 64 Vectored interrupts
- 8 Levels interrupt priority

#### Flexible I/O

- 11 GPIO pins
- All GPIO pins can be programmable as input or output individually
- All GPIO pins are internal pull-up/pull-down selectable individually
- CMOS/TTL level schmitt triggered input
- External wake up/interrupt on all GPIOs

#### **Peripheral Feature**

- One Full Speed USB OTG controller
- Four Multi-function 32-bit timers, support capture and PWM mode
- Three full-duplex advanced UART(DMA)
- One SPI interface supports host and device mode (DMA)
- One IIC interface supports host and device mode
- RTC, with alarm clock and time base to wake up the chip
- 16-bit PWM generator for motor driving
- Three IQ Encoder
- 5 channels 10-bit ADC
- 1 channel 8 levels Low Power Detector
- Embedded PMU support low power mode
- Watchdog
- Power-on reset

# requirement Support GFSK and π/4 DQPSK all packet

V5.4+BR+EDR+BLE specification

Bluetooth Piconet and Scatternet support

Meet class2 and class3 transmitting power

Compliant with Bluetooth

- Maximum +8dBm transmitting power
- EDR receiver with -93dBm sensitivity
- Support a2dp\avctp\avdtp\avrcp\hfp\spp\smp\
  att\gap\gatt\rfcomm\sdp\l2cap profile

#### **Power Supply**

VDDIO is 1.8V to 3.4V

#### **Packages**

SOP16

#### **Temperature**

- Operating temperature: -40°C to +85°C
- Storage temperature: -65°C to +150°C

#### **Bluetooth Feature**

 CMOS single-chip fully-integrated radio and baseband

#### **Confidential**

## 1. Block Diagram

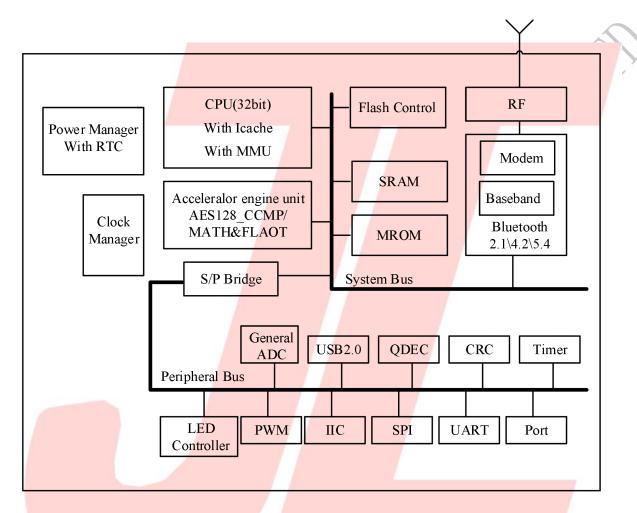


Figure 1-1 AC6329E\_SOP16 Block Diagram

## 2. Pin Definition

### 2.1 Pin Assignment

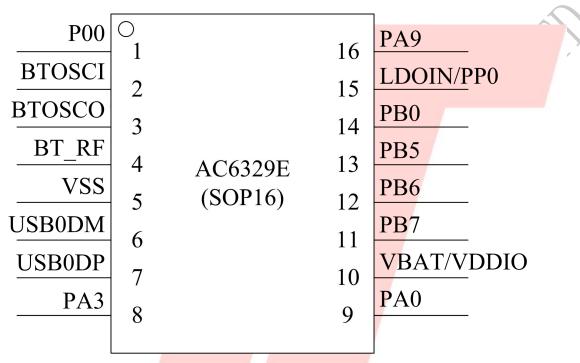


Figure 2-1 AC6329E SOP16 Package Diagram

### 2.2 Pin Description

Table 2-1 AC6329E\_SOP16 Pin Description

PIN NO.	Name	I/O Type	Function	Other Function
1	P00	I/O	GPIO (High Voltage)	
2	BTOSCI	I	BTOSCI	
3	BTOSCO	О	BTOSCO	-
4	BT_RF	-	RF Antenna	-
5	VSS	P	GND	-
6	USB0DM	I/O	GPIO (pull down)	IIC_SDA_A: IIC SDA(A); ADC11: ADC Channel 11; UART1_RXD: Uart1 Data In(D);
7	USB0DP	I/O	GPIO (pull down)	IIC_SCL_A: IIC SCL(A); ADC10: ADC Channel 10; UART1_TXD: Uart1 Data Out(D);
8	PA3	I/O	GPIO	CAP2: Timer2 Capture; IIC_SCL_D: IIC SCL(D); ADC1: ADC Channel 1; UART2_TXA: Uart2 Data Out(A); PWMCH0L;
9	PA0	I/O	GPIO (High Voltage)	CLKOUT1; UART2_TXB: Uart2 Data Out(B); UART2_RXB: Uart2 Data In(B); PWMCH0H;
Vi	VBAT	P	LDO Power	-
10	VDDIO	Р	IO Power 3.3V	-
11	PB7	I/O	GPIO (High Voltage)	SPI2_DOA: SPI2 Data Out(A); UART2_RXC: Uart2 Data In(C);
12	PB6	I/O	GPIO	SPI2_CLKA: SPI2 Clock(A); ADC12: ADC Channel 12; UART2_TXC: Uart2 Data Out(C); TMR3CK;
13	PB5	I/O	GPIO (High Voltage)	SPI2_DIA: SPI2 Data In(A); UART1_RXA: Uart1 Data In(A); PWMCH3L;

14	PB0	I/O	GPIO (High Voltage )	CLKOUT0; UART1_TXB: Uart1 Data Out(B); TMR2CK;
15	LDOIN/PP0	P	Charge Power 5V	PWM3: Timer3 PWM Output;  UART0_TXD: Uart0 Data Out(D);  UART0_RXD: Uart0 Data In(D);
16	PA9	I/O	GPIO	Long Press Reset;
10	1 A9	1/0	(pull up)	ADC8: ADC Channel 8;

## 3. Electrical Characteristics

### 3.1 Absolute Maximum Ratings

Table 3-1

Symbol	Par	ameter	Min	Max	Unit
Topt	Operating temperature		-40	+85	°C
Tstg	Storage temperature		-65	+150	°C
LDOIN	Charge Input Voltage		-0.3	6	V
VDDIO	3.3V IO Input Voltage		-0.3	3.6	V

Note: The chip can be damaged by any stress in excess of the absolute maximum ratings listed below

### 3.2 Recommended Operating Conditions

Table 3-2

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
LDOIN	Voltage Input	4.5	5.0	5.5	V	_
VDDIO	Voltage Input	1.8	3.0	3.4	V	
Ivddio	Loading current	33.2	_	60	mA	

### 3.3 IO Input/Output Electrical Logical Characteristics

**Table 3-3** 

IO input characteristics								
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions		
$V_{IL}$	Low-Level Input Voltage	-0.3	_	0.3* VDDIO	V	VDDIO = 3.3V		
$ m V_{IH}$	High-Level Input Voltage	0.7* VDDIO	-	VDDIO+0.3	V	VDDIO = 3.3V		
IO output o	characteristi <mark>cs</mark>							
V <sub>OL</sub>	Low-Level Output Voltage	-	, i –	0.33	V	VDDIO = 3.3V		
$V_{\mathrm{OH}}$	High-Level Output Voltage	2.7	_	7-/	V	VDDIO = 3.3V		

### 3.4 Internal Resistor Characteristics

Table 3-4

Port	Drive Strength	Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment
PA1-PA9, PB6,	drive_select[11] 24mA drive_select[10] 24mA (with 120ohm res) drive_select[01] 8mA drive_select[00] 8mA (with 120ohm res)	10K	10K	PA9 default pull up     USB0DM&USB0DP     default pull down     Internal pull-up/pull-down
PA0,PB0, PB5,PB7, P00,PP0	8mA	10K	10K	resistance   accuracy ±20% 4. PA0,PB0,PB5,PB7,P00,PP 0 can pull-up resistance to 5V
USB0DP	4mA	1.5K	15K	
USB0DM	4mA	180K	15K	

### 3.5 BT Characteristics

### 3.5.1 Transmitter

**Basic Rate** 

**Table 3-5** 

Paramet	er	Min	Тур	Max	Unit	<b>Test Conditions</b>
RF Transmit	Power	-	4	6	dBm	
RF Power Contr	ol Range	-	20	-	dB	25°C,
20dB Bandy	vidth		950	<del>-</del>	KHz	Power Supply
In-band spurious	$F=F_0\pm 1MHz$	4	-20	/ /-	dBm	VBAT=3.7V
Emissions	$F=F_0\pm 2MHz$	-	-45	-	dBm	2441MHz
(BQB Test Mode	F=F <sub>0</sub> ±3MHz	. / -	-35	-	dBm	DH5
RF_Tx Power=4dBm)	$F=F_0\pm>3MHz$	-	-40	-	dBm	

Enhanced Data Rate

Table 3-6

Paramete	er	Min	Тур	Max	Unit	Test Conditions
Relative Power		-	-1	-	dB	
π/4 DQPSK	DEVM RMS	-	4	-	%	25°C,
	DEVM 99%	- 7	12	- /	%	Power Supply
Modulation Accuracy	DEVM Peak	- /	9	- /	%	
In-band spurious	F=F <sub>0</sub> ±1MHz	-/ /	-4	- 7	dBm	VBAT=3.7V
Emissions	F=F <sub>0</sub> ±2MHz	7/	-30		dBm	2441MHz
(BQB Test Mode	$F=F_0\pm 3MHz$	7-/	-30	, / <u>-</u>	dBm	2DH5
RF_Tx Power=4dBm)	$F=F_0\pm>3MHz$	7 1	-37	-	dBm	

### 3.5.2 Receiver

**Basic Rate** 

**Table 3-7** 

Paramete	r	Min	Тур	Max	Unit	Test Conditions
Sensitivit	y	-	-91	-	dBm	
Co-channel Interferen	ice Rejection	-	6	-	dB	25°C,
	+1MHz	-	-7	-	dB	Power Supply
	-1MHz	-	-7	-	dB	
Adjacent Channel	+2MHz	-	-37	-	dB	VBAT=3.7V
selectivity C/I	-2MHz	- //	-39	<del></del>	dB	2441MHz
	+3MHz	1	-32	/ /-	dB	DH5
	-3MHz	-	-43	-	dB	

### **Enhanced Data Rate**

### Table 3-8

Paramete	r	Min	Тур	Max	Unit	<b>Test Conditions</b>
Sensitivit	y	-	-93	-	dBm	
Co-channel Interferer	ace Rejection	-	8	-	dB	25°C,
	+1MHz	-	-14	-	dB	Power Supply
	-1MHz	-	-15	-	dB	
Adjacent Channel	+2MHz	- /	-36	- /	dB	VBAT=3.7V
selectivity C/I	-2MHz	- /	-39	- 7	dB	2441MHz
	+3MHz	-///	-29	-/	dB	2DH5
	-3MHz	4/	-43	7	dB	

### 3.5.3 BLE

### 1M Data Rate

**Table 3-9** 

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivi	Sensitivity		-95	-	dBm	
RF Transmit	Power	-	6.5	8	dBm	
In-band Spurious	M-N =2MHz	-	-35	-	dBm	
Emission	M-N ≥3MHz	-	-33	-	dBm	25°C
	Δfl avg	-	250	-	KHz	Power Supply
Modulation Characteristics	Δf2 99%	- /	210	7-7-	KHz	VBAT=3.7V
Characteristics	Δflavg/Δf2avg	4	0.9	/ -	/	2440MHz
Carrier Frequency Offset		-15	- /	+15	KHz	
Frequency Drift		-25	- 1	+25	KHz	
Frequency Dri	ft Rate	-5	-/ /	+5	KHz/50us	

### 2M Data Rate

### **Table 3-10**

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivity		-	-92	-	dBm	
RF Transmit F	ower	-	6.5	8	dBm	
	M-N =4MHz	-	-40	- /	dBm	
In-band Spurious  Emission	M-N =5MHz	-	-40	- /	dBm	25°C
Elinission	M-N ≥6MHz	-///	-40	-	dBm	Power Supply
	Δfl avg	- /- /-	500	/-	KHz	
Modulation Characteristics	Δf2 99%	/-/	430	-	KHz	VBAT=3.7V
Characteristics	Δflavg/Δf2avg	1 1	0.9	-	/	2440MHz
Carrier Frequency Offset		-20	-	+20	KHz	
Frequency Drift		-25	-	+25	KHz	
Frequency Drift	ft Rate	-5	-	+5	KHz/50us	

### **Long Range**

**Table 3-11** 

Parameter	Min	Тур	Max	Unit	Test Conditions
Sensitivity LE 125K(S8)	-	-102	-	dBm	VBAT=3.7V,25°C
Sensitivity LE 500K(S2)	-	-99	-	dBm	2440MHz

# 4. Package Information

### 4.1 SOP16(9.9mm\*6mm)

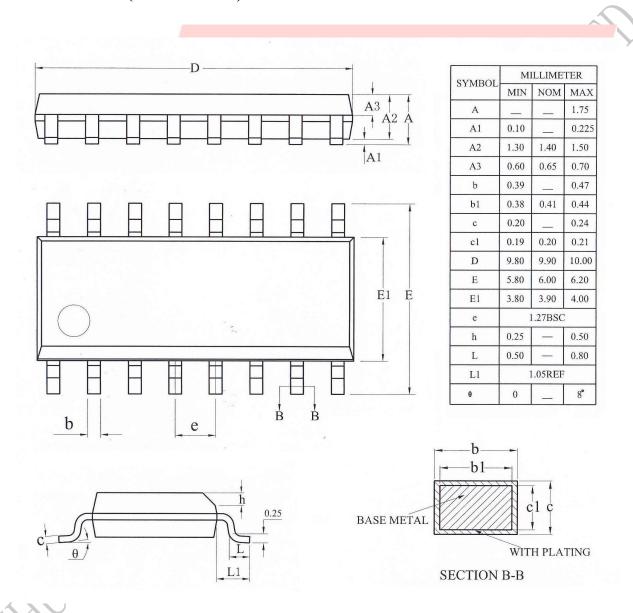


Figure 4-1 AC6329E\_SOP16 Package

# 5. Package Type Specification



- ①Represents different packages
- $@ Represents \ different \ memory \ sizes$ 
  - 2: 2Mbit Flash

# 6. Revision History

Date	Revision	Description
2021.03.18	V1.0	Initial Release
2022.07.19	V1.1	Update Bluetooth Feature
2023.11.28	V1.2	Add BLE parameter
2023.12.13	V1.3	Update Bluetooth Feature
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